

N-CHANNEL MOS FIELD EFFECT POWER TRANSISTOR

2SK797

DESCRIPTION The 2SK797 is N-Channel MOS Field Effect Power Transistor designed for solenoid, motor and lamp driver.

- FEATURES**
- Gate Drive — Logic level —
 - Low $R_{DS(on)}$
 - No Secondary Breakdown

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

Storage Temperature -55 to $+150$ °C

Channel Temperature 150 °C Maximum

Maximum Power Dissipations

Total Power Dissipation ($T_a = 25$ °C) 3.0 W

Total Power Dissipation ($T_c = 25$ °C) 150 W

Maximum Voltages and Currents ($T_a = 25$ °C)

V_{DS} Drain to Source Voltage 60 V

V_{GS} Gate to Source Voltage ± 20 V

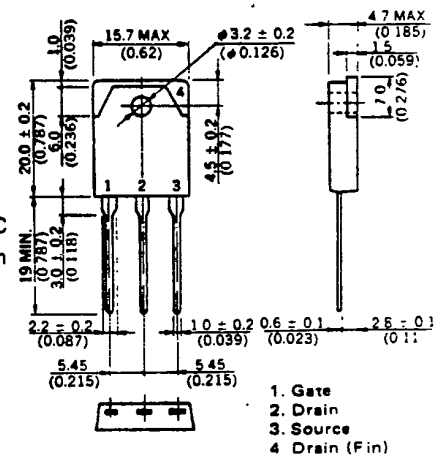
$I_{D(DC)}$ Drain Current (DC) ± 40 A

$I_{D(pulse)}$ Drain Current (pulse)* ± 160 A

* $PW \leq 300$ μs , Duty Cycle ≤ 2 %

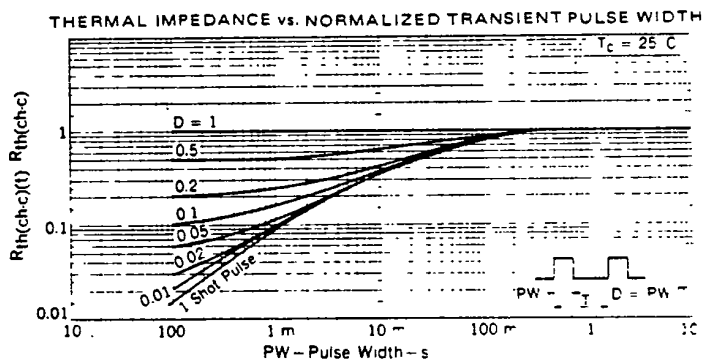
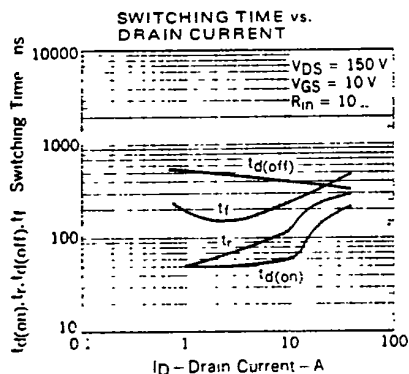
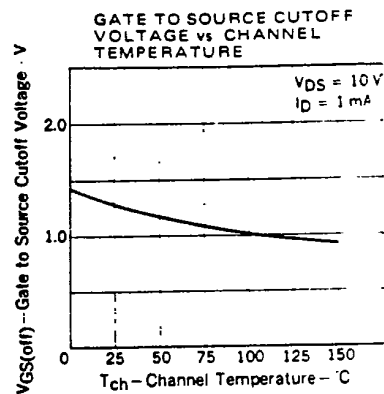
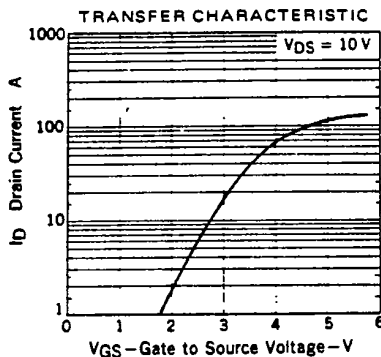
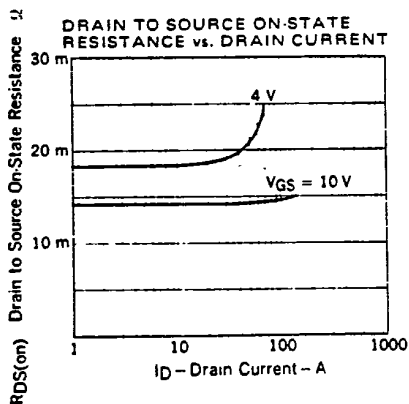
PACKAGE DIMENSIONS

in millimeters (inches)



ELECTRICAL CHARACTERISTICS ($T_a = 25$ °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX	UNIT	TEST CONDITIONS
$R_{DS(on)}$	Drain to Source On-State Resistance			18	m Ω	$V_{GS} = 10$ V, $I_D = 20$ A
$R_{DS(on)}$	Drain to Source On-State Resistance			22	m Ω	$V_{GS} = 4$ V, $I_D = 20$ A
$V_{GS(off)}$	Gate to Source Cutoff Voltage	1.0		2.5	V	$V_{DS} = 10$ V, $I_D = 1$ mA
Y_{fs}	Forward Transfer Admittance	5.0			S	$V_{DS} = 10$ V, $I_D = 20$ A
I_{DSS}	Drain Leakage Current			100	μ A	$V_{DS} = 60$ V, $V_{GS} = 0$
I_{GSS}	Gate to Source Leakage Current			± 100	nA	$V_{GS} = \pm 20$ V, $V_{DS} = 0$
C_{iss}	Input Capacitance		8000		pF	$V_{DS} = 10$ V
C_{oss}	Output Capacitance		2400		pF	$V_{GS} = 0$
C_{rss}	Reverse Transfer Capacitance		700		pF	$f = 1$ MHz
$t_{d(on)}$	Turn-On Delay Time		60		ns	$I_D = 20$ A, $V_{CC} = 50$ V $R_L = 2.5$ Ω $R_{in} = 10$ Ω
t_r	Rise Time		120		ns	
$t_{d(off)}$	Turn-Off Delay Time		400		ns	
t_f	Fall Time		250		ns	



SWITCHING TIME TEST CIRCUIT

